

In the Claims

Claim 1 (currently amended): A method of forming a semiconductor construction, comprising:

forming a mass over a semiconductor substrate, the mass comprising a memory bit which includes a first magnetic layer, a second magnetic layer, and a non-magnetic layer between the first and second magnetic layers;

forming first and second layers over the mass, and over a region of the substrate proximate the mass;

removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;

etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and

forming a material within the channel.

Claim 2 (canceled).

Claim 3 (original): The method of claim 1 wherein the removing the first and second layers from over the mass comprises chemical-mechanical polishing of the first and second layers.

Claim 4 (original): The method of claim 1 wherein the first layer comprises silicon dioxide and the second layer comprises silicon nitride.

Claim 5 (original): The method of claim 1 wherein the first layer comprises silicon nitride and the second layer comprises silicon dioxide.

Claim 6 (original): The method of claim 1 wherein the second layer comprises silicon carbide and the first layer does not comprise silicon carbide.

Claim 7 (original): The method of claim 1 wherein the second layer consists essentially of one or both of silicon and carbon; and wherein the first layer consists essentially of silicon and one or both of nitrogen and oxygen.

Claim 8 (original): The method of claim 1 wherein the second layer consists essentially of silicon and one or both of nitrogen and oxygen; and wherein the first layer comprises carbon.

Claim 9 (original): The method of claim 1 wherein the material formed within the channel is a soft magnetic material comprising one or more of nickel, iron and copper.

Claim 10 (original): The method of claim 1 wherein the material formed within the channel consists essentially of mu-metal.

Claims 11-77 (cancelled).

Claim 78 (new): A method of forming a semiconductor construction, comprising:

forming a mass over a semiconductor substrate;

forming first and second layers over the mass, and over a region of the substrate proximate the mass;

removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass, the removing of the first and second layers from over the mass comprising chemical-mechanical polishing of the first and second layers;

etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and

forming a material within the channel.

Claim 79 (new): A method of forming a semiconductor construction, comprising:

- forming a mass over a semiconductor substrate;
- forming first and second layers over the mass, and over a region of the substrate proximate the mass; the first layer comprising silicon nitride and the second layer comprising silicon dioxide;
- removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;
- etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and
- forming a material within the channel.

Claim 80 (new): A method of forming a semiconductor construction, comprising:

forming a mass over a semiconductor substrate;

forming first and second layers over the mass, and over a region of the substrate proximate the mass; the second layer comprising silicon carbide and the first layer not comprising silicon carbide;

removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;

etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and

forming a material within the channel.

Claim 81 (new): A method of forming a semiconductor construction, comprising:

forming a mass over a semiconductor substrate;

forming first and second layers over the mass, and over a region of the substrate proximate the mass; the second layer consisting essentially of one or both of silicon and carbon, and the first layer consisting essentially of silicon and one or both of nitrogen and oxygen;

removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;

etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and

forming a material within the channel.

Claim 82 (new): A method of forming a semiconductor construction, comprising:

forming a mass over a semiconductor substrate;

forming first and second layers over the mass, and over a region of the substrate proximate the mass; the second layer consisting essentially of silicon and one or both of nitrogen and oxygen, and the first layer comprising carbon;

removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;

etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and

forming a material within the channel, the material comprising one or more of nickel, iron and copper.

Claim 83 (new): A method of forming a semiconductor construction, comprising:

- forming a mass over a semiconductor substrate;
- forming first and second layers over the mass, and over a region of the substrate proximate the mass;
- removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;
- etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and
- forming a material within the channel; said material being a soft magnetic material comprising one or more of nickel, iron and copper.

Claim 84 (new): A method of forming a semiconductor construction, comprising:

- forming a mass over a semiconductor substrate;
- forming first and second layers over the mass, and over a region of the substrate proximate the mass;
- removing the first and second layers from over the mass while leaving portions of the first and second layers over the region proximate the mass;
- etching the first layer with an etch selective for the first layer relative to the second layer to remove at least some of the first layer from under the second layer and thereby form a channel over the region proximate the mass; and
- forming a material within the channel; said material consisting essentially of mu-metal.